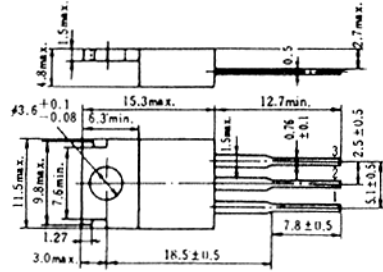


2SB1078 (K)

SILICON PNP EPITAXIAL

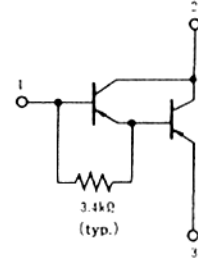
LOW FREQUENCY POWER AMPLIFIER

COMPLEMENTARY PAIR WITH 2SD1377 (K)



(JEDEC TO-220AB)

1. Base
 2. Collector (Flange)
 3. Emitter
- (Dimensions in mm)

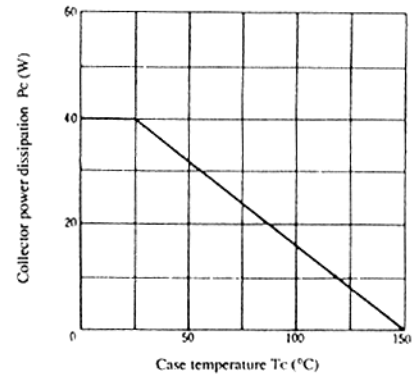


■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB1078 (K)	Unit
Collector to base voltage	VCBO	-120	V
Collector to emitter voltage	VCEO	-120	V
Emitter to base voltage	VEBO	-7	V
Collector current	IC	-8	A
Collector peak current	iC(peak)	-12	A
Collector power dissipation	PC*	40	W
Junction temperature	Tj	150	°C
Storage temperature	Tsg	-55 to +150	°C

* Value at Tc = 25°C

MAXIMUM COLLECTOR DISSIPATION CURVE

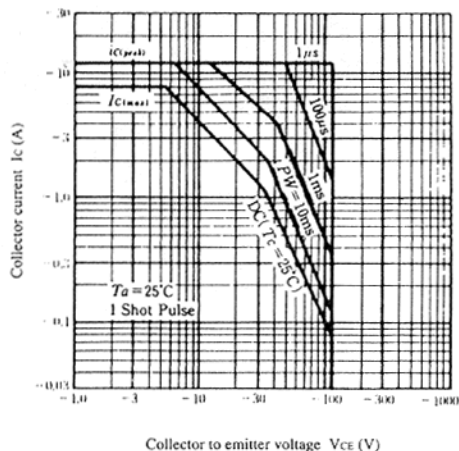


■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

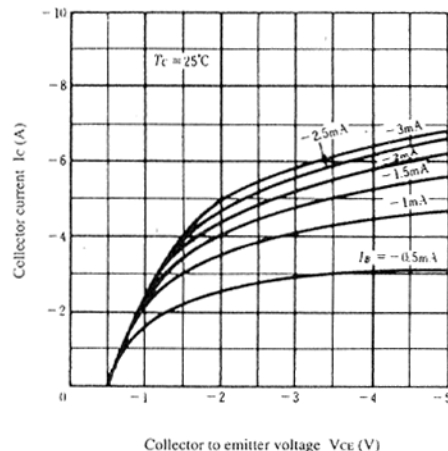
Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to emitter breakdown voltage	V(BR)CEO	IC = -25mA, RBE = ∞	-120	—	—	V
Emitter to base breakdown voltage	V(BR)EBO	IE = -50mA, IC = 0	-7	—	—	V
Collector cutoff current	ICBO	VCE = -120V, IE = 0	—	—	-100	μA
	ICEO	VCE = -100V, RBE = ∞	—	—	-10	μA
DC current transfer ratio	hFE	VCE = -3V, IC = -4A*	1000	—	20000	
Collector to emitter saturation voltage	VCE(sat)1	IC = -4A, IB = -8mA*	—	—	-1.5	V
	VCE(sat)2	IC = -8A, IB = -80mA*	—	—	-3.0	V
Base to emitter saturation voltage	VBE(sat)1	IC = -4A, IB = -8mA*	—	—	-2.0	V
	VBE(sat)2	IC = -8A, IB = -80mA*	—	—	-3.5	V
Turn on time	ton	IC = -4A, IB1 = -IB2 = -8mA	—	1.5	—	μs
Storage time	tsg		—	2.0	—	μs
Fall time	tf		—	0.5	—	μs

* Pulse Test.

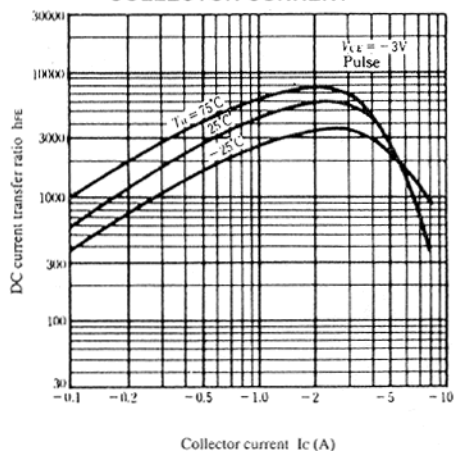
AREA OF SAFE OPERATION



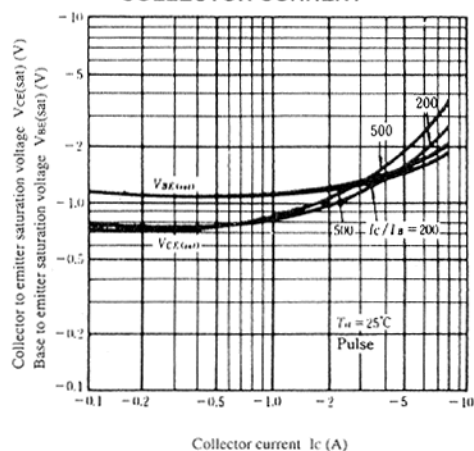
TYPICAL OUTPUT CHARACTERISTICS



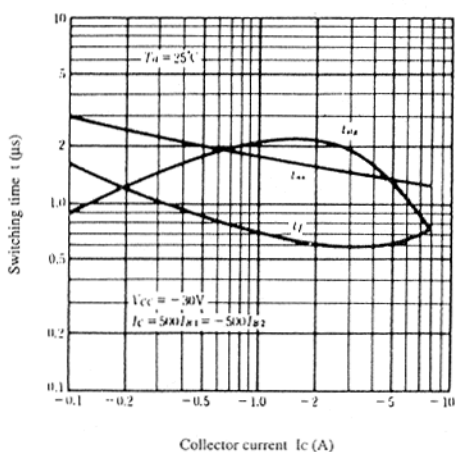
DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



SATURATION VOLTAGE VS. COLLECTOR CURRENT



SWITCHING TIME VS. COLLECTOR CURRENT



TRANSIENT THERMAL RESISTANCE

